



STP3NB100 STP3NB100FP

N-CHANNEL 1000V - 5.3Ω - 3A TO-220/TO-220FP

PowerMesh™ MOSFET

PRELIMINARY DATA

| TYPE | V _{DSS} | R _{DS(on)} | I _D |
|-------------|------------------|---------------------|----------------|
| STP3NB100 | 1000 V | < 6 Ω | 3 A |
| STP3NB100FP | 1000 V | < 6 Ω | 3 A |

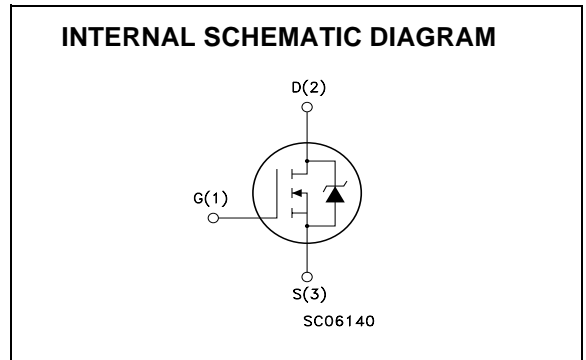
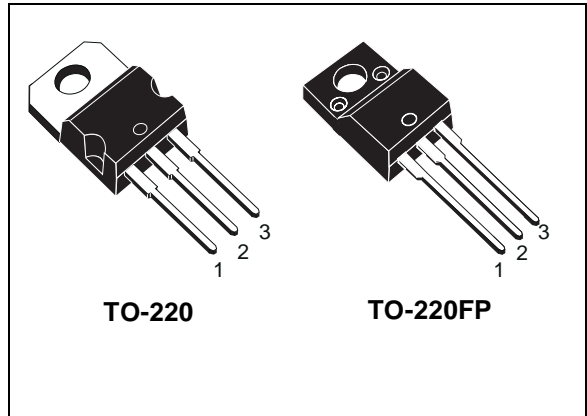
- TYPICAL R_{DS(on)} = 5.3Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED

DESCRIPTION

Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprietary edge termination structure, gives the lowest R_{DS(on)} per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | | Unit |
|---------------------|--|------------|-------------|------|
| | | STP3NB100 | STP3NB100FP | |
| V _{DS} | Drain-source Voltage (V _{GS} = 0) | 1000 | | V |
| V _{DGR} | Drain-gate Voltage (R _{GS} = 20 kΩ) | 1000 | | V |
| V _{GS} | Gate- source Voltage | ±30 | | V |
| I _D | Drain Current (continuous) at T _C = 25°C | 3 | 3 (*) | A |
| I _D | Drain Current (continuous) at T _C = 100°C | 1.9 | 1.9 (*) | A |
| I _{DM} (▲) | Drain Current (pulsed) | 12 | 12 | A |
| P _{TOT} | Total Dissipation at T _C = 25°C | 100 | 35 | W |
| | Derating Factor | 0.8 | 0.28 | W/°C |
| dv/dt (1) | Peak Diode Recovery voltage slope | 4.5 | 4.5 | V/ns |
| V _{ISO} | Insulation Withstand Voltage (DC) | - | 2500 | V |
| T _{stg} | Storage Temperature | -65 to 150 | | °C |
| T _j | Max. Operating Junction Temperature | 150 | | °C |

(*)Pulse width limited by safe operating area

(*)Limited only by maximum temperature allowed

(1) I_{SD} ≤ 3A, di/dt ≤ 200A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.

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This is preliminary information on a new product now in development or undergoing evaluation. Details are subject to change without notice.

STP3NB100/FP

THERMAL DATA

| | | TO-220 | TO-220FP | |
|----------------|--|--------|----------|------|
| Rthj-case | Thermal Resistance Junction-case Max | 1.25 | 3.57 | °C/W |
| Rthj-amb | Thermal Resistance Junction-ambient Max | 62.5 | | °C/W |
| T _l | Maximum Lead Temperature For Soldering Purpose | 300 | | °C |

AVALANCHE CHARACTERISTICS

| Symbol | Parameter | Max Value | Unit |
|-----------------|--|-----------|------|
| I _{AR} | Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max) | 3 | A |
| E _{AS} | Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V) | 244 | mJ |

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|----------------------|---|---|------|------|---------|----------|
| V _{(BR)DSS} | Drain-source Breakdown Voltage | I _D = 250 μA, V _{GS} = 0 | 1000 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current (V _{GS} = 0) | V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C | | | 1 50 | μA μA |
| I _{GSS} | Gate-body Leakage Current (V _{DS} = 0) | V _{GS} = ±30V | | | ±100 | nA |

ON ⁽¹⁾

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|-----------------------------------|---|------|------|------|------|
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} , I _D = 250 μA | 2 | 3 | 4 | V |
| R _{DS(on)} | Static Drain-source On Resistance | V _{GS} = 10V, I _D = 1.5 A | | 5.3 | 6 | Ω |

DYNAMIC

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------------------------------|------------------------------|---|------|------|------|------|
| g _{fs} ⁽¹⁾ | Forward Transconductance | V _{DS} > I _{D(on)} × R _{DS(on)max} , I _D = 1.7 A | | 2.8 | | S |
| C _{iss} | Input Capacitance | V _{DS} = 25V, f = 1 MHz, V _{GS} = 0 | | 700 | | pF |
| C _{oss} | Output Capacitance | | | 80 | | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 8 | | pF |

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-------------|--------------------|--|------|------|------|------|
| $t_{d(on)}$ | Turn-on Delay Time | $V_{DD} = 500\text{ V}$, $I_D = 1.5\text{ A}$ $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3) | | 18 | | ns |
| t_r | Rise Time | | | 12 | | ns |
| Q_g | Total Gate Charge | $V_{DD} = 800\text{ V}$, $I_D = 3\text{ A}$, $V_{GS} = 10\text{ V}$ | | 22 | 30 | nC |
| Q_{gs} | Gate-Source Charge | | | 6 | | nC |
| Q_{gd} | Gate-Drain Charge | | | 10.5 | | nC |

SWITCHING OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------|-----------------------|--|------|------|------|------|
| $t_{r(Voff)}$ | Off-voltage Rise Time | $V_{DD} = 800\text{ V}$, $I_D = 3\text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 5) | | 22 | | ns |
| t_f | Fall Time | | | 28 | | ns |
| t_c | Cross-over Time | | | 30 | | ns |

SOURCE DRAIN DIODE

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-----------------|-------------------------------|---|------|------|------|---------------|
| I_{SD} | Source-drain Current | | | | 3 | A |
| $I_{SDM}^{(1)}$ | Source-drain Current (pulsed) | | | | 12 | A |
| $V_{SD}^{(2)}$ | Forward On Voltage | $I_{SD} = 3\text{ A}$, $V_{GS} = 0$ | | | 1.6 | V |
| t_{rr} | Reverse Recovery Time | $I_{SD} = 3\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 100\text{ V}$, $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5) | | 580 | | ns |
| Q_{rr} | Reverse Recovery Charge | | | 2.9 | | μC |
| I_{RRM} | Reverse Recovery Current | | | 10 | | A |

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

Fig. 1: Unclamped Inductive Load Test Circuit

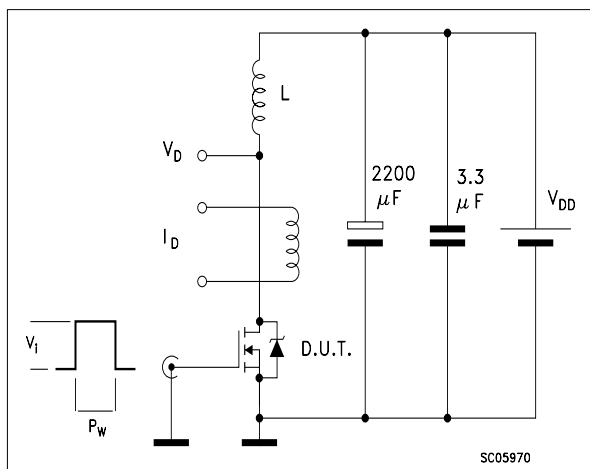


Fig. 2: Unclamped Inductive Waveform

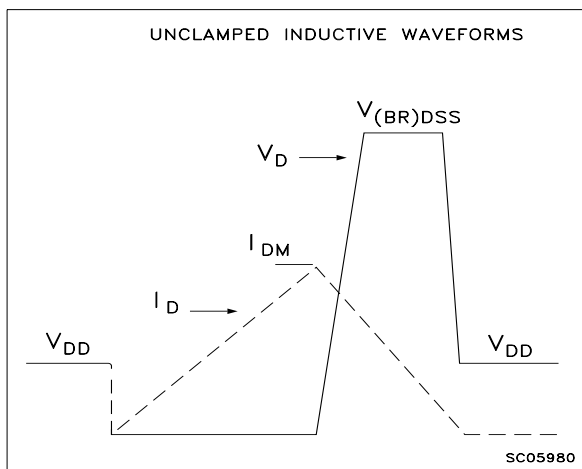


Fig. 3: Switching Times Test Circuit For Resistive Load

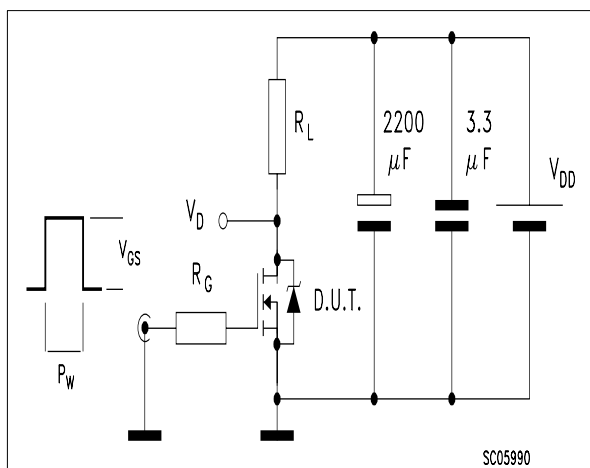


Fig. 4: Gate Charge test Circuit

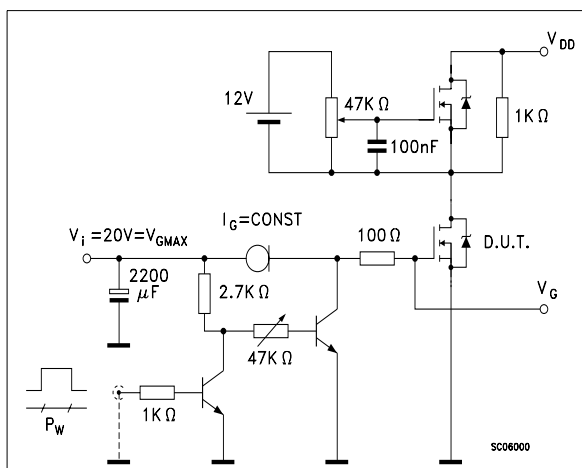
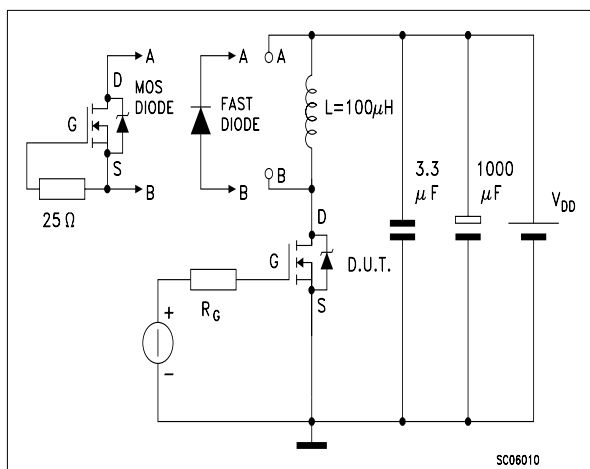
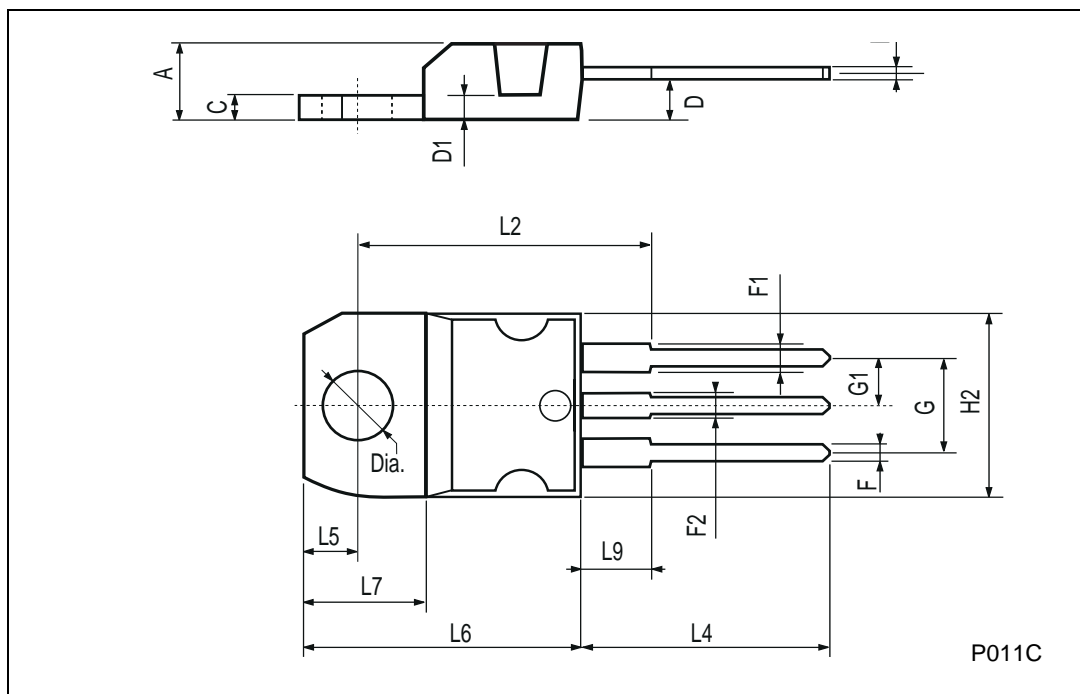


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



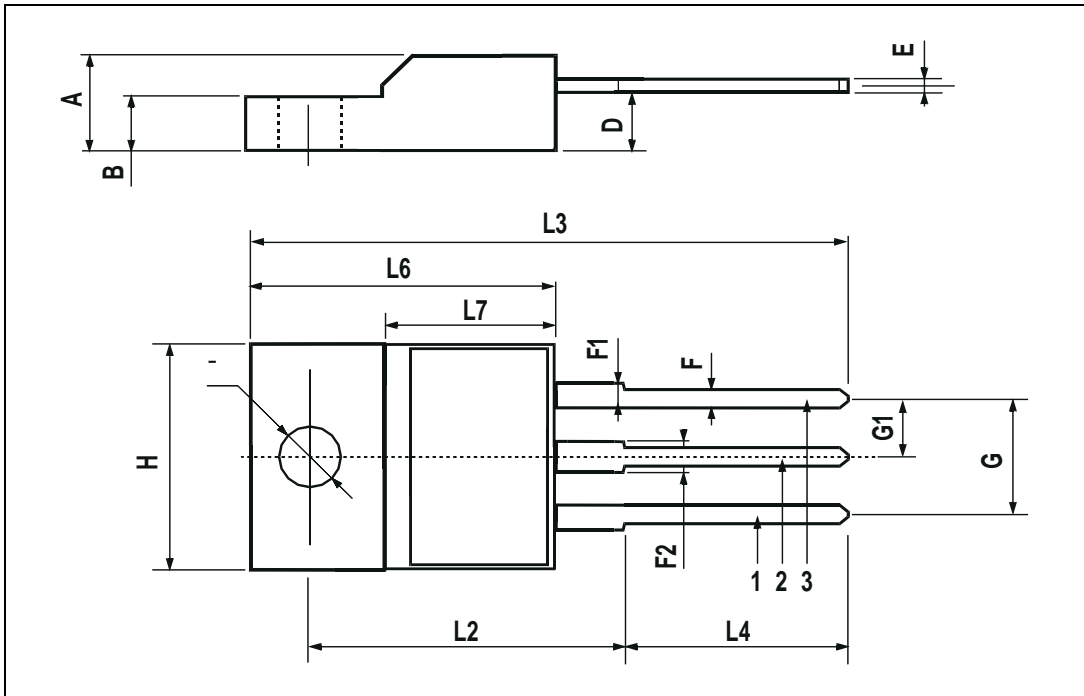
TO-220 MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|-------|------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.40 | | 4.60 | 0.173 | | 0.181 |
| C | 1.23 | | 1.32 | 0.048 | | 0.051 |
| D | 2.40 | | 2.72 | 0.094 | | 0.107 |
| D1 | | 1.27 | | | 0.050 | |
| E | 0.49 | | 0.70 | 0.019 | | 0.027 |
| F | 0.61 | | 0.88 | 0.024 | | 0.034 |
| F1 | 1.14 | | 1.70 | 0.044 | | 0.067 |
| F2 | 1.14 | | 1.70 | 0.044 | | 0.067 |
| G | 4.95 | | 5.15 | 0.194 | | 0.203 |
| G1 | 2.4 | | 2.7 | 0.094 | | 0.106 |
| H2 | 10.0 | | 10.40 | 0.393 | | 0.409 |
| L2 | | 16.4 | | | 0.645 | |
| L4 | 13.0 | | 14.0 | 0.511 | | 0.551 |
| L5 | 2.65 | | 2.95 | 0.104 | | 0.116 |
| L6 | 15.25 | | 15.75 | 0.600 | | 0.620 |
| L7 | 6.2 | | 6.6 | 0.244 | | 0.260 |
| L9 | 3.5 | | 3.93 | 0.137 | | 0.154 |
| DIA. | 3.75 | | 3.85 | 0.147 | | 0.151 |



TO-220FP MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.4 | | 4.6 | 0.173 | | 0.181 |
| B | 2.5 | | 2.7 | 0.098 | | 0.106 |
| D | 2.5 | | 2.75 | 0.098 | | 0.108 |
| E | 0.45 | | 0.7 | 0.017 | | 0.027 |
| F | 0.75 | | 1 | 0.030 | | 0.039 |
| F1 | 1.15 | | 1.7 | 0.045 | | 0.067 |
| F2 | 1.15 | | 1.7 | 0.045 | | 0.067 |
| G | 4.95 | | 5.2 | 0.195 | | 0.204 |
| G1 | 2.4 | | 2.7 | 0.094 | | 0.106 |
| H | 10 | | 10.4 | 0.393 | | 0.409 |
| L2 | | 16 | | | 0.630 | |
| L3 | 28.6 | | 30.6 | 1.126 | | 1.204 |
| L4 | 9.8 | | 10.6 | 0.385 | | 0.417 |
| L6 | 15.9 | | 16.4 | 0.626 | | 0.645 |
| L7 | 9 | | 9.3 | 0.354 | | 0.366 |
| ∅ | 3 | | 3.2 | 0.118 | | 0.126 |



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